

Description

The ASMDA3.3C is a Bi-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The ASMDA3.3C complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a lead-free SO-8 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

Features

- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 20A (8/20 μs)
- RoHS Compliant

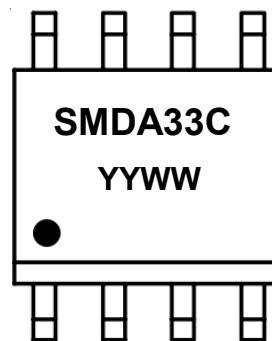
Mechanical Characteristics

- Package: SO-8
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Peripherals
- Industrial Equipment
- Notebook Computers
- Portable Instrumentation
- Microprocessor Based Equipment
- Cell Phone Handsets and Accessories
- Personal Digital Assistants (PDAs) and Pagers

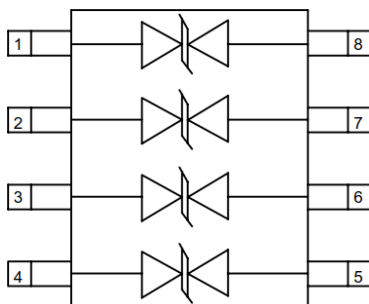
Marking Information



Ordering Information

Part Number	Packaging	Reel Size
ASMDA3.3C	2500/Tape & Reel	13 inch

Dimensions and Pin Configuration



SO-8 (Top View)

Circuit and Pin Schematic

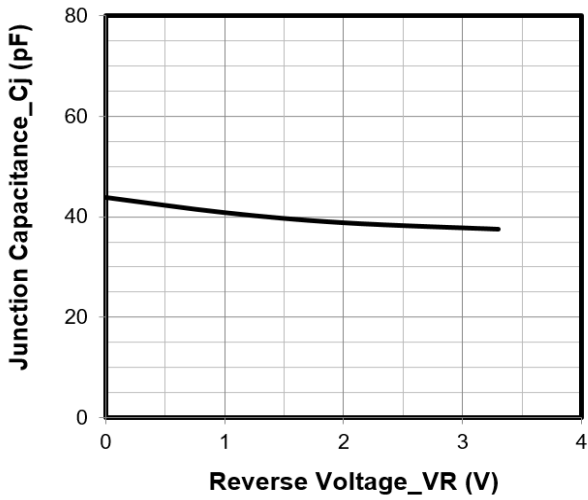
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	300	W
Peak Pulse Current (8/20 μs)	I _{PP}	20	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	± 30 ± 30	kV
Operating Temperature Range	T _J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^{\circ}\text{C}$

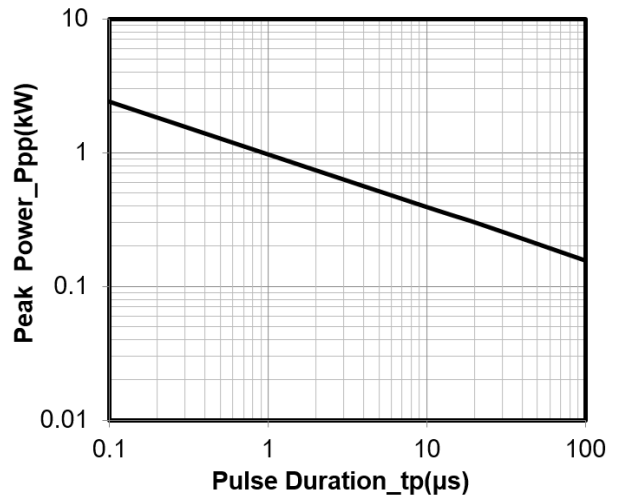
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Reverse Breakdown Voltage	V _{BR}	3.5			V	I _T = 1mA
Reverse Leakage Current	I _R			0.5	μA	V _{RWM} = 3.3V
Clamping Voltage	V _C			8	V	I _{PP} = 1A (8 x 20 μs pulse)
Clamping Voltage	V _C			15	V	I _{PP} = 20A (8 x 20 μs pulse)
Junction Capacitance	C _J		40		pF	V _R = 0V, f = 1MHz

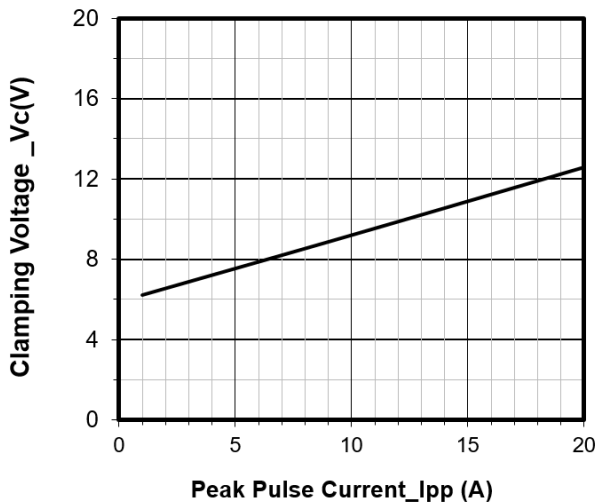
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



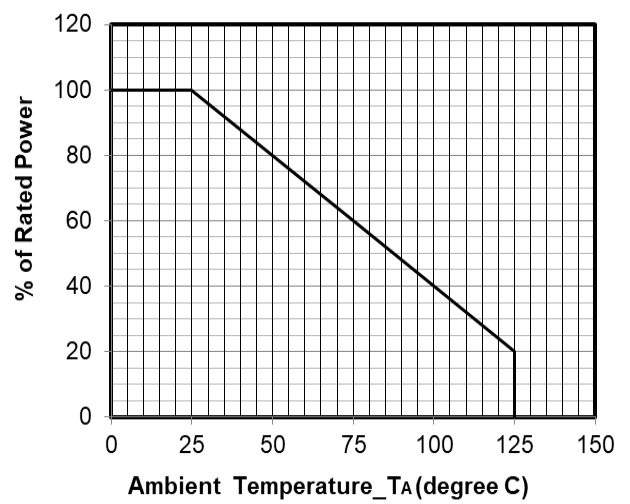
Junction Capacitance vs. Reverse Voltage



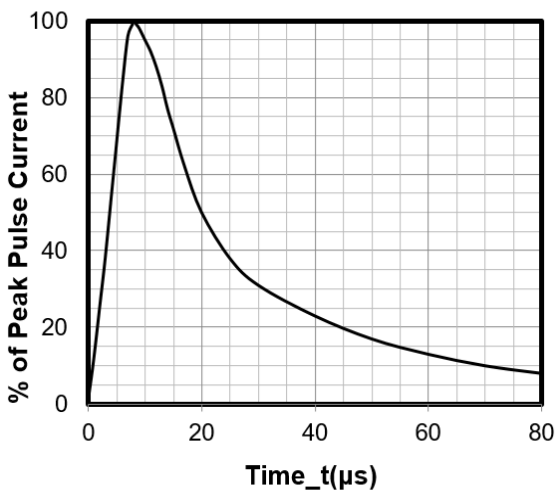
Peak Pulse Power vs. Pulse Time



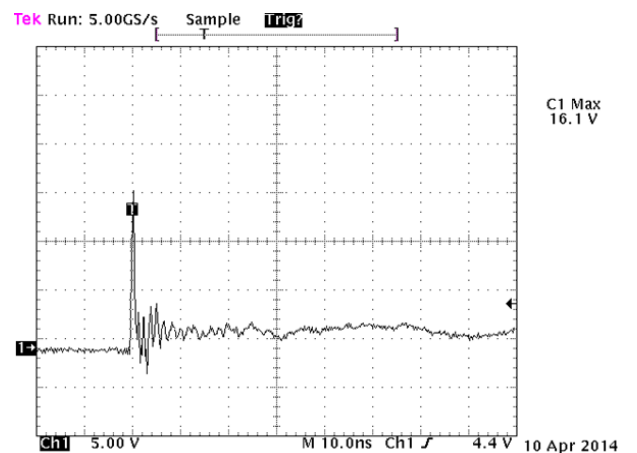
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



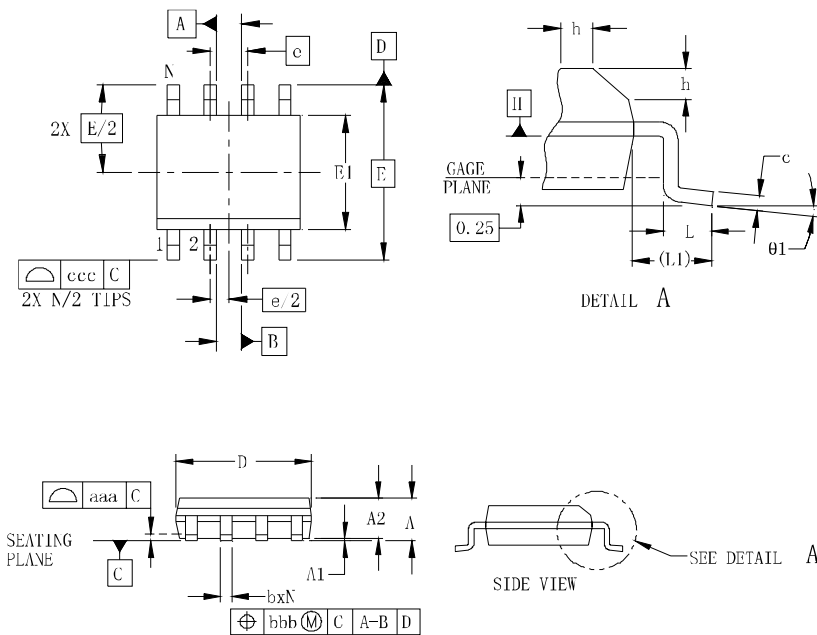
8 X 20μs Pulse Waveform



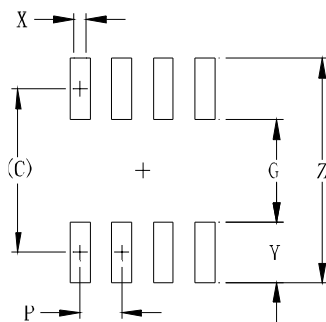
Note: Data is taken with a 10x attenuator

ESD Clamping Voltage

8 kV Contact per IEC61000-4-2

SO-8 Package Outline Drawing


SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.35		1.75	0.053		0.069
A1	0.10		0.25	0.004		0.010
A2	1.25		1.65	0.049		0.065
b	0.31		0.51	0.012		0.020
c	0.17		0.25	0.007		0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
E	6.00 BSC			0.236 BSC		
e	1.27 BSC			0.050 BSC		
h	0.25		0.50	0.010		0.020
L	0.40	0.72	1.04	0.016	0.028	0.041
L1	(1.04)			(0.041)		
N	8			8		
theta1	0°		8°	0°		8°
aaa	0.10			0.004		
bbb	0.25			0.010		
ccc	0.20			0.008		

Suggested Land Pattern


SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	(5.20)	0.205
G	3.00	0.118
P	1.27	0.050
X	0.60	0.024
Y	2.20	0.087
Z	7.40	0.291

Contact Information

Applied Power Microelectronics Inc.

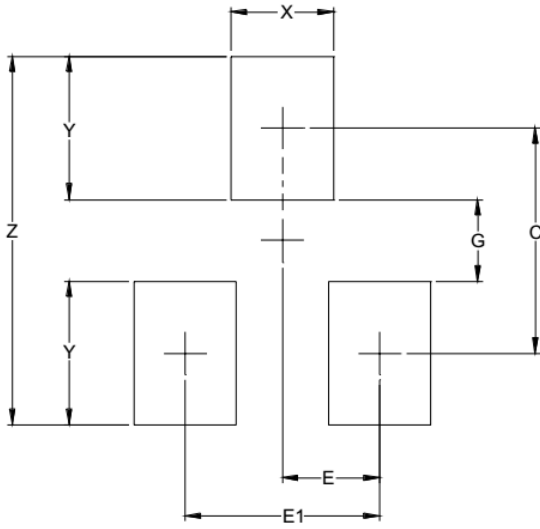
 Website: <http://www.appliedpowermicro.com>

 Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606

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Suggested Land Pattern



SYM	DIMENSIONS	
	INCHES	MILLIMETERS
C	.087	2.20
E	.037	0.95
E1	.075	1.90
G	.031	0.80
X	.039	1.00
Y	.055	1.40
Z	.141	3.60

Contact Information

Applied Power Microelectronics Inc.

Website: <http://www.appliedpowermicro.com>

Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606